

Automotive Dual N-Channel 40 V (D-S) 175 °C MOSFETs

PRODUCT SUMMARY

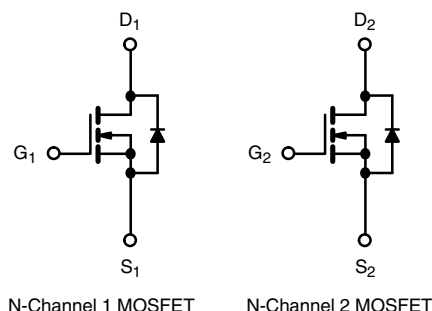
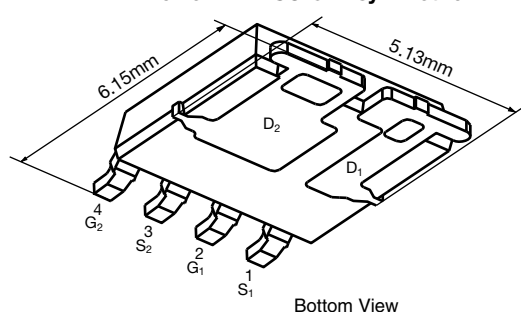
	N-CHANNEL 1	N-CHANNEL 2
V_{DS} (V)	40	40
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.0160	0.0064
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5$ V	0.0188	0.0076
I_D (A)	15	18
Configuration	Dual N	

FEATURES

- TrenchFET® Power MOSFET
- AEC-Q101 Qualified^d
- 100 % R_g and UIS Tested
- Material categorization:
For definitions of compliance please see www.vishay.com/doc?99912



PowerPAK® SO-8L Asymmetric



ORDERING INFORMATION

Package	PowerPAK SO-8L Dual Asymmetric
Lead (Pb)-free and Halogen-free	SQJ940EP-T1-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER		SYMBOL	N-CHANNEL 1	N-CHANNEL 2	UNIT
Drain-Source Voltage		V _{DS}	40	40	V
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current ^a	T _C = 25 °C	I _D	15	18	A
	T _C = 125 °C		15	10.5	
Continuous Source Current (Diode Conduction) ^a		I _S	15	39	
Pulsed Drain Current ^b		I _{DM}	60	72	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	20.5	35.5	
Single Pulse Avalanche Energy		E _{AS}	21	63	mJ
Maximum Power Dissipation ^b	T _C = 25 °C	P _D	48	43	W
	T _C = 125 °C		16	14	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175		°C
Soldering Recommendations (Peak Temperature) ^{e, f}			260		

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	N-CHANNEL 1	N-CHANNEL 2	UNIT
Junction-to-Ambient	R_{thJA}	70	70	°C/W
Junction-to-Case (Drain)	R_{thJC}	3.3	3.5	

Notes

- Package limited.
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR4 material).
- Parametric verification ongoing.
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)								
PARAMETER	SYMBOL	TEST CONDITIONS			MIN.	TYP.	MAX.	UNIT
Static								
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		N-Ch 1	40	-	-	V
		V _{GS} = 0 V, I _D = 250 μA		N-Ch 2	40	-	-	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		N-Ch 1	1.5	2	2.5	
		V _{DS} = V _{GS} , I _D = 250 μA		N-Ch 2	1.5	2	2.5	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		N-Ch 1	-	-	± 100	nA
				N-Ch 2	-	-	± 100	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} 40 V	N-Ch 1	-	-	1	μA
		V _{GS} = 0 V	V _{DS} = - 40 V	N-Ch 2	-	-	1	
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 125 °C	N-Ch 1	-	-	50	
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 125 °C	N-Ch 2	-	-	50	
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	N-Ch 1	-	-	150	
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	N-Ch 2	-	-	150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	N-Ch 1	30	-	-	A
		V _{GS} = 10 V	V _{DS} ≥ 5 V	N-Ch 2	30	-	-	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 15 A	N-Ch 1	-	0.0133	0.0160	Ω
		V _{GS} = 10 V	I _D = 20 A	N-Ch 2	-	0.0053	0.0064	
		V _{GS} = 10 V	I _D = 15 A, T _J = 125 °C	N-Ch 1	-	-	0.0270	
		V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	N-Ch 2	-	-	0.0105	
		V _{GS} = 10 V	I _D = 15 A, T _J = 175 °C	N-Ch 1	-	-	0.0334	
		V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	N-Ch 2	-	-	0.0130	
		V _{GS} = 4.5 V	I _D = 13 A	N-Ch 1	-	0.0157	0.0188	
		V _{GS} = 4.5 V	I _D = 18 A	N-Ch 2	-	0.0063	0.0076	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 15 A		N-Ch 1	-	64	-	S
		V _{DS} = 15 V, I _D = 20 A		N-Ch 2	-	102	-	
Dynamic ^b								
Input Capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 20 V, f = 1 MHz	N-Ch 1	-	717	896	pF
		V _{GS} = 0 V	V _{DS} = 20 V, f = 1 MHz	N-Ch 2	-	1850	2313	
Output Capacitance	C _{oss}	V _{GS} = 0 V	V _{DS} = 20 V, f = 1 MHz	N-Ch 1	-	118	148	
		V _{GS} = 0 V	V _{DS} = 20 V, f = 1 MHz	N-Ch 2	-	272	340	
Reverse Transfer Capacitance	C _{rss}	V _{GS} = 0 V	V _{DS} = 20 V, f = 1 MHz	N-Ch 1	-	48	60	
		V _{GS} = 0 V	V _{DS} = 20 V, f = 1 MHz	N-Ch 2	-	98	123	
Total Gate Charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 20 V, I _D = 6 A	N-Ch 1	-	13.5	20	nC
		V _{GS} = 10 V	V _{DS} = 20 V, I _D = 16 A	N-Ch 2	-	31.8	48	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	V _{DS} = 20 V, I _D = 6 A	N-Ch 1	-	2.24	-	
		V _{GS} = 10 V	V _{DS} = 20 V, I _D = 16 A	N-Ch 2	-	5.5	-	
Gate-Drain Charge ^c	Q _{gd}	V _{GS} = 10 V	V _{DS} = 20 V, I _D = 6 A	N-Ch 1	-	2.06	-	
		V _{GS} = 10 V	V _{DS} = 20 V, I _D = 16 A	N-Ch 2	-	4.7	-	
Gate Resistance	R _g	f = 1 MHz		N-Ch 1	1.2	2.52	5	Ω
				N-Ch 2	3	7.93	13	

Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

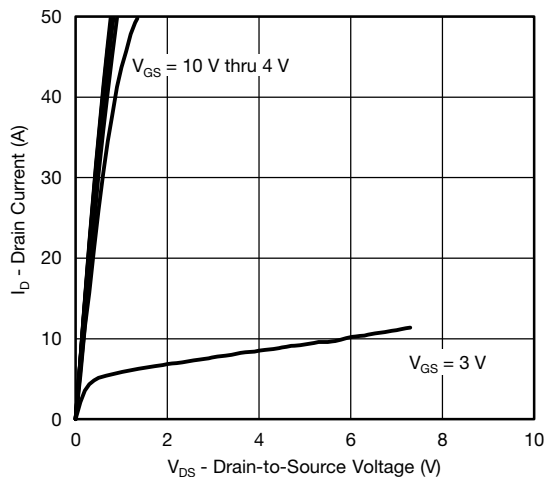
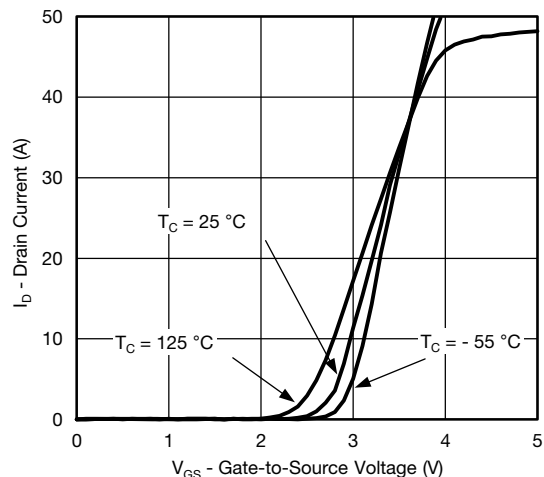
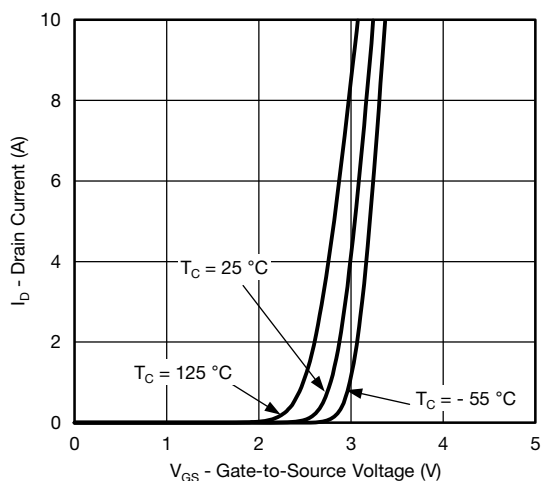
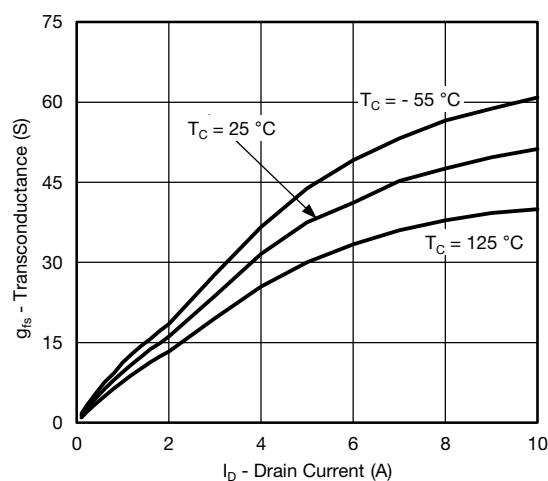
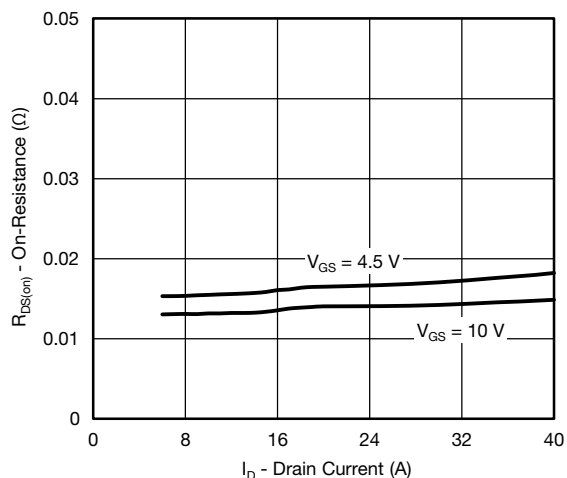
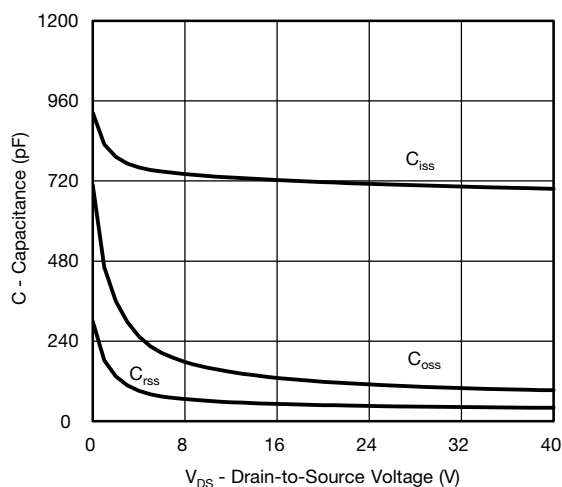


SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 20 V, R _L = 20 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 1	-	4.8	7.2	ns
		V _{DD} = 20 V, R _L = 20 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 2	-	7.7	11.6	
Rise Time ^c	t _r	V _{DD} = 20 V, R _L = 20 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 1	-	9.3	14	
		V _{DD} = 20 V, R _L = 20 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 2	-	9.5	14.3	
Turn-Off Delay Time ^c	t _{d(off)}	V _{DD} = 20 V, R _L = 20 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 1	-	15.6	23.4	
		V _{DD} = 20 V, R _L = 20 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 2	-	47	70	
Fall Time ^c	t _f	V _{DD} = 20 V, R _L = 20 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 1	-	4.9	7.4	
		V _{DD} = 20 V, R _L = 20 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 2	-	13.5	20.3	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed Current ^a	I _{SM}		N-Ch 1	-	-	60	A
			N-Ch 2	-	-	72	
Forward Voltage	V _{SD}	I _F = 8 A, V _{GS} = 0 V	N-Ch 1	-	0.8	1.2	V
		I _F = 17 A, V _{GS} = 0 V	N-Ch 2	-	0.8	1.2	

Notes

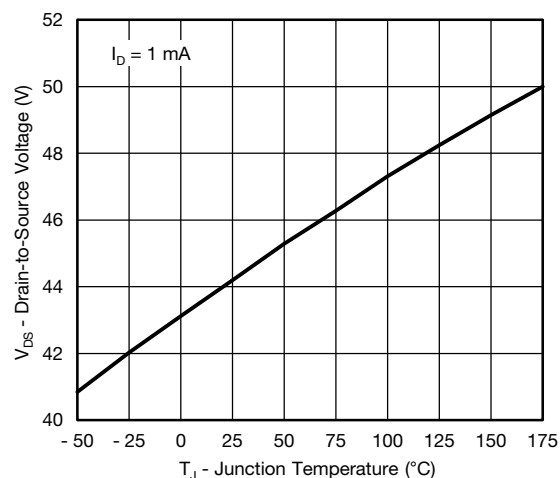
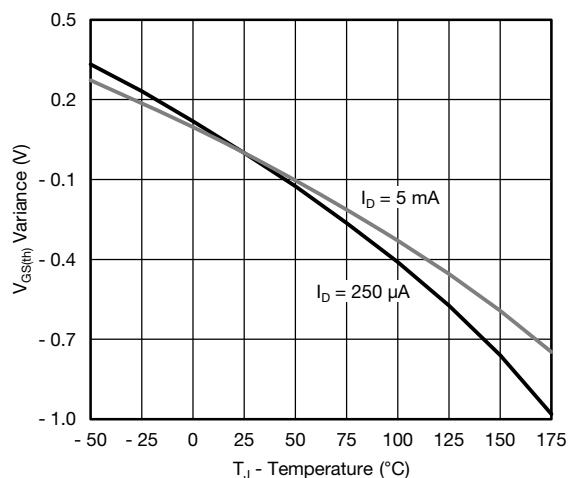
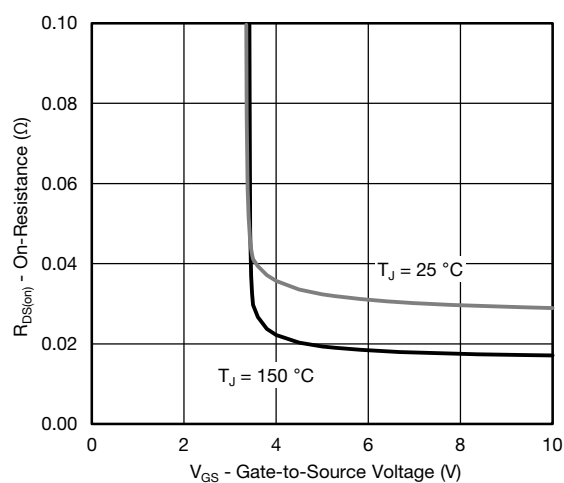
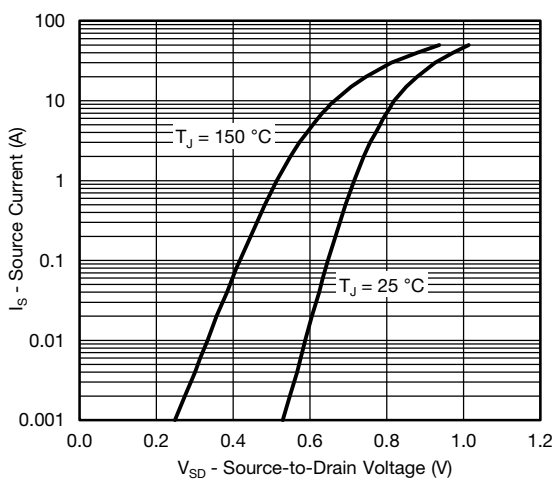
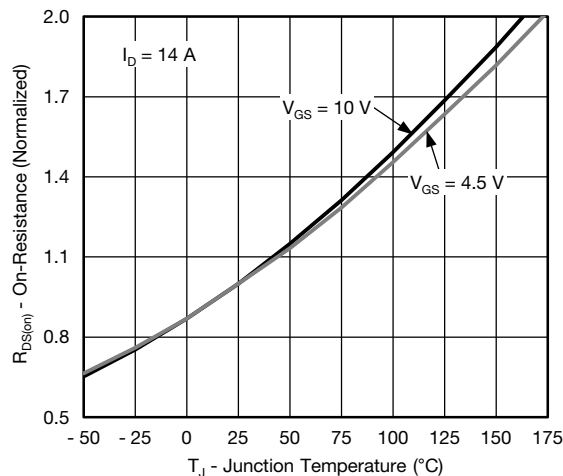
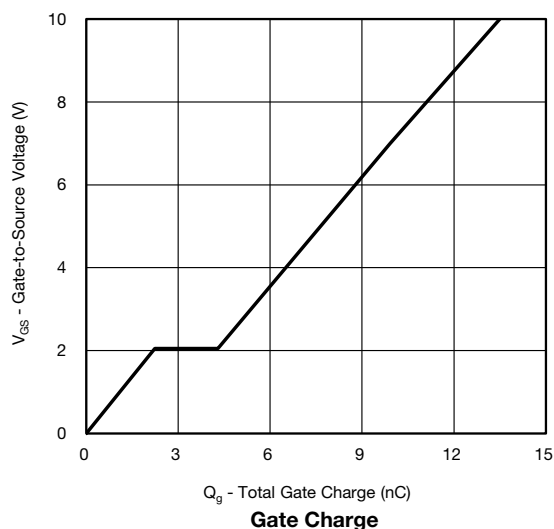
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

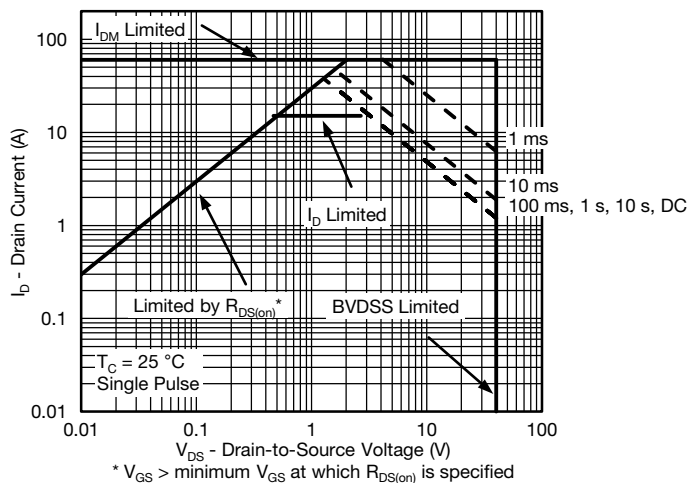
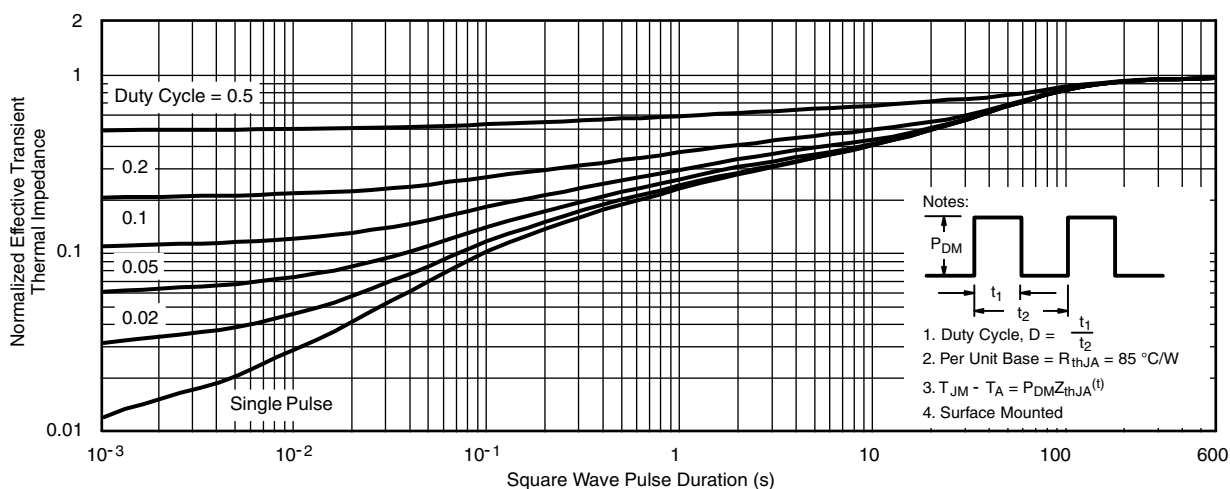
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

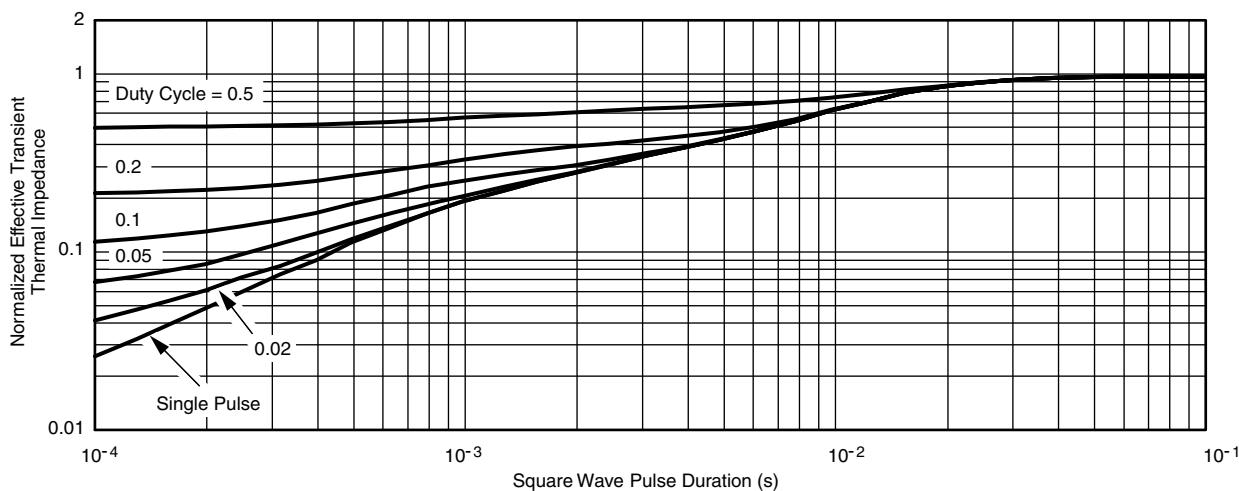
N-CHANNEL 1 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Output Characteristics

Transfer Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

Capacitance



N-CHANNEL 1 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



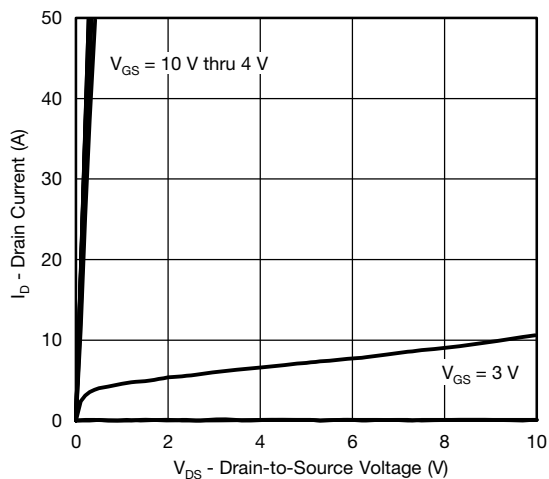
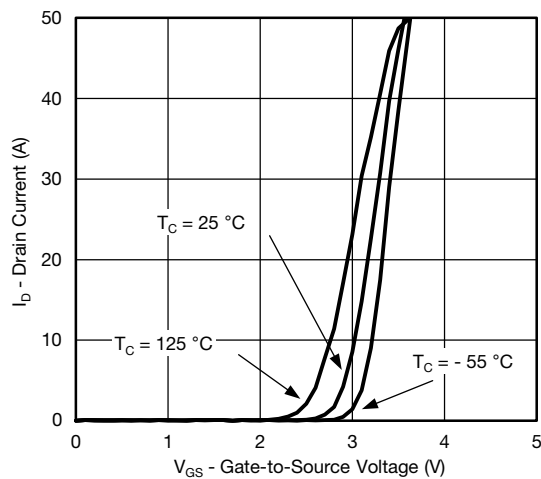
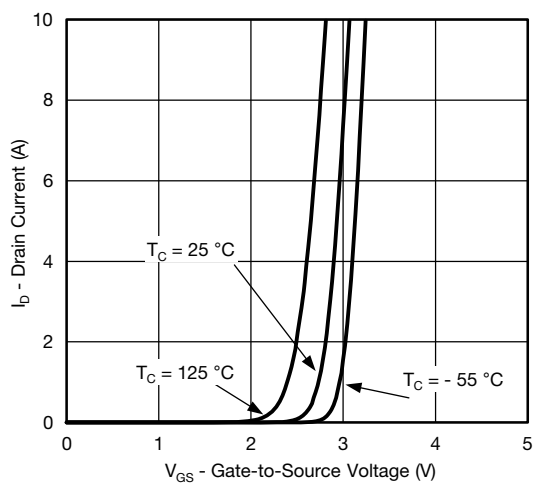
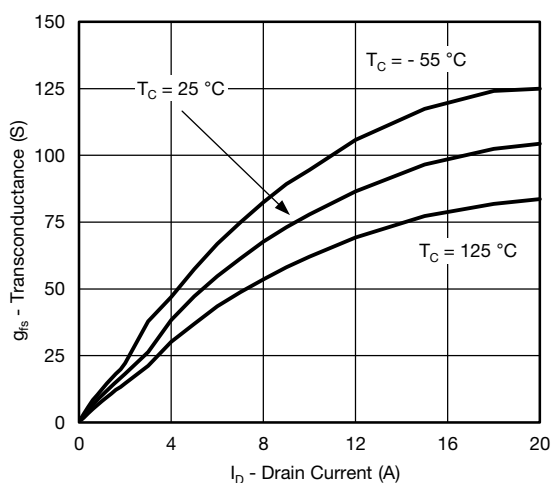
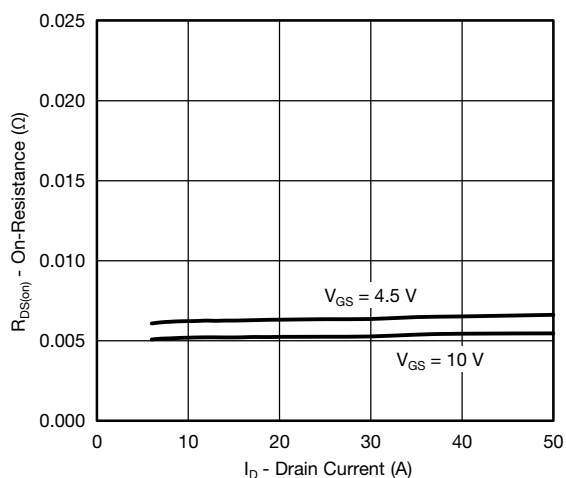
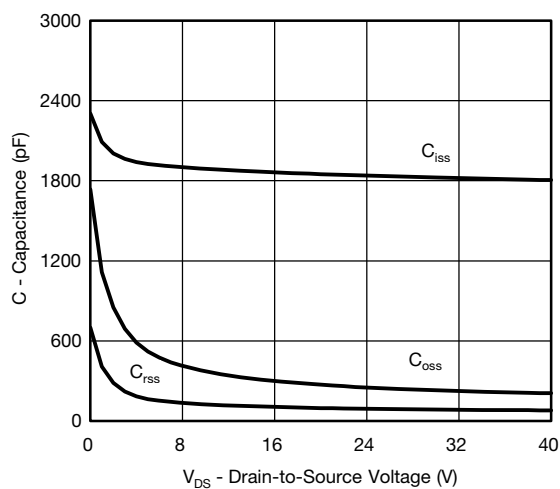
N-CHANNEL 1 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Safe Operating Area

Normalized Thermal Transient Impedance, Junction-to-Ambient

N-CHANNEL 1 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)


Normalized Thermal Transient Impedance, Junction-to-Case

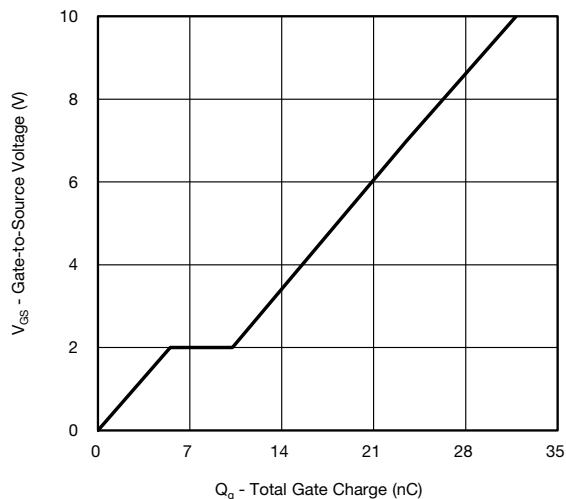
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Case ($25\text{ }^{\circ}\text{C}$)
 are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

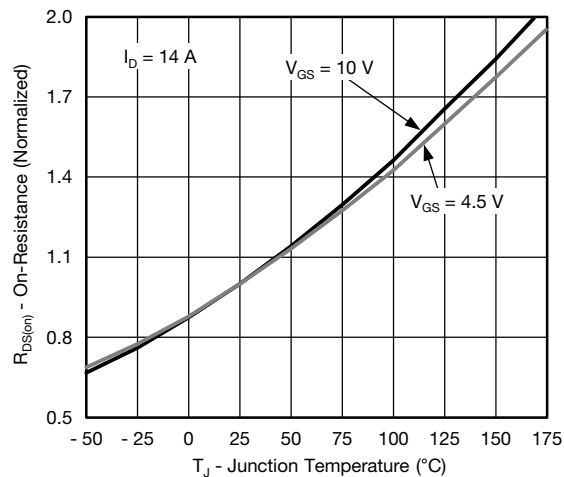
N-CHANNEL 2 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Output Characteristics

Transfer Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

Capacitance



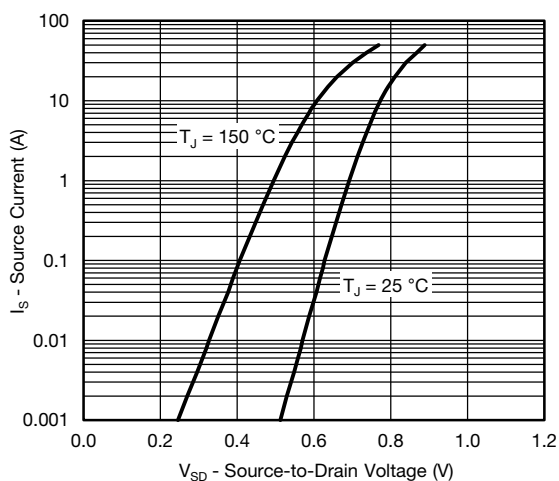
N-CHANNEL 2 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



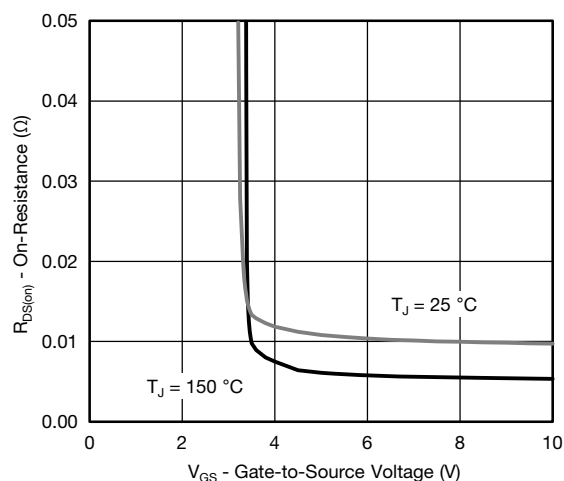
Gate Charge



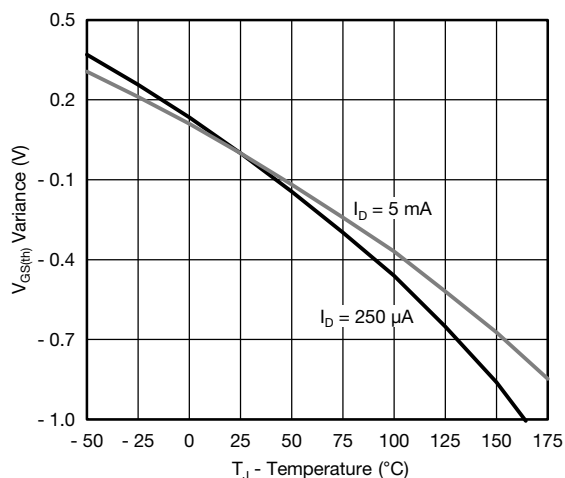
On-Resistance vs. Junction Temperature



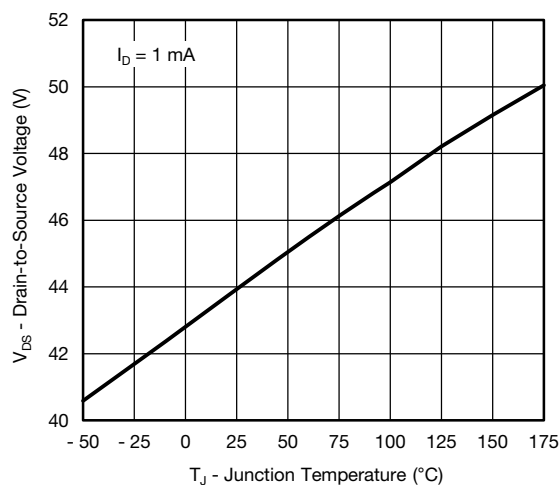
Source Drain Diode Forward Voltage



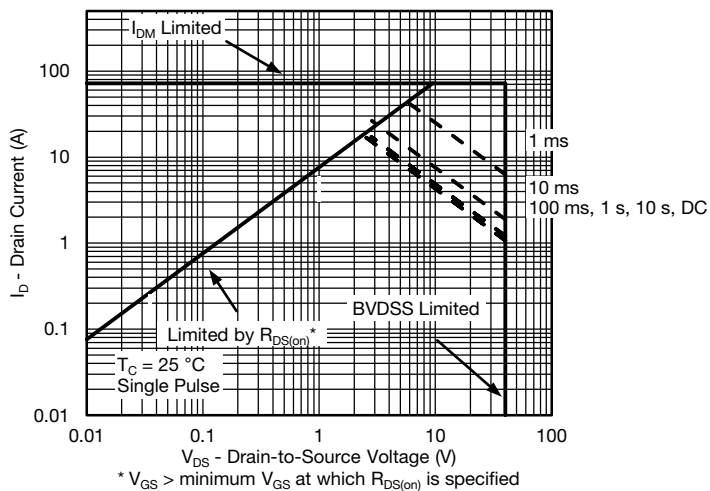
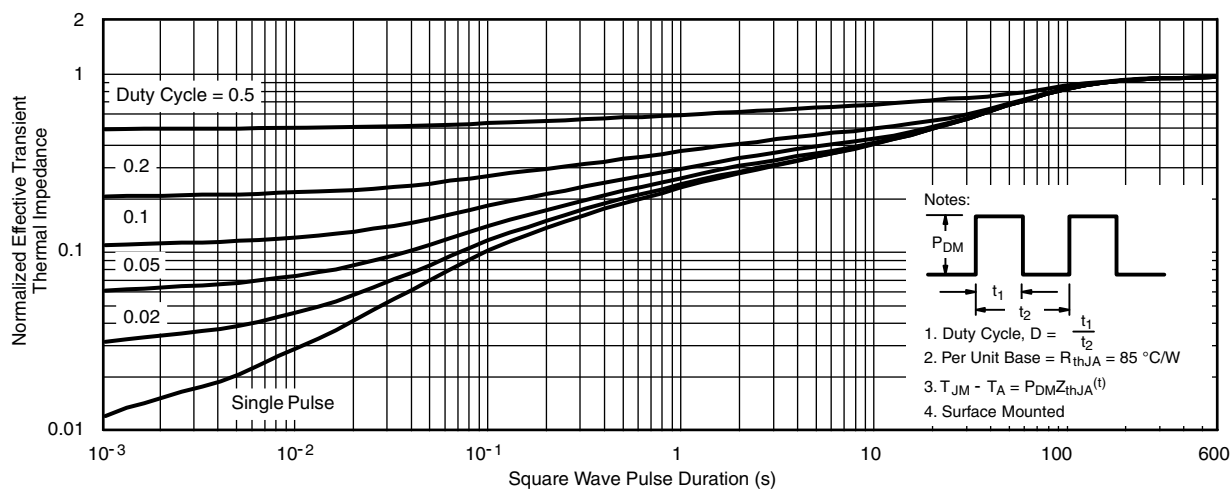
On-Resistance vs. Gate-to-Source Voltage

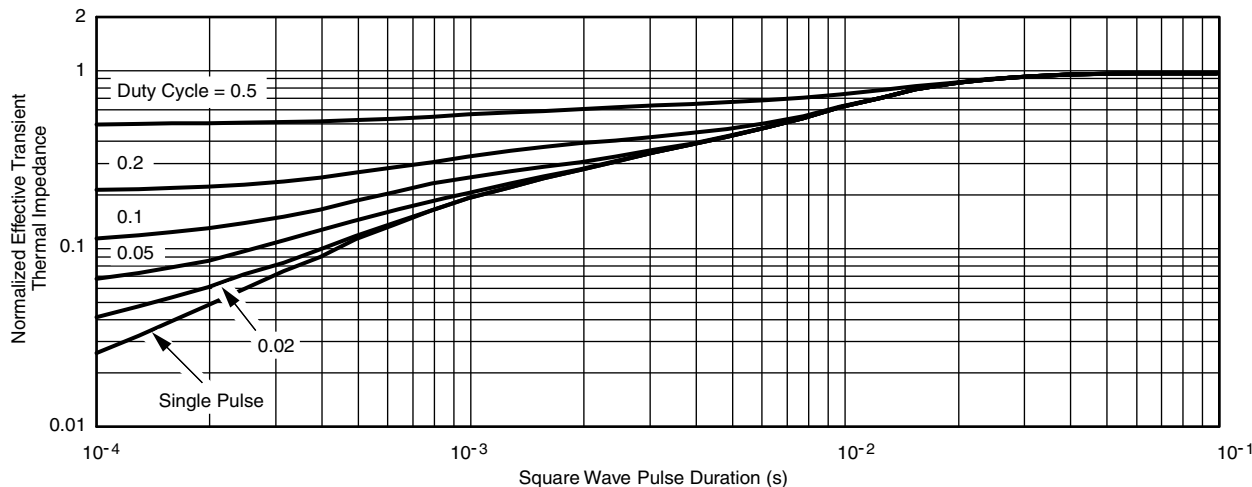


Threshold Voltage



Drain Source Breakdown vs. Junction Temperature

N-CHANNEL 2 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Safe Operating Area

Normalized Thermal Transient Impedance, Junction-to-Ambient

N-CHANNEL 2 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)


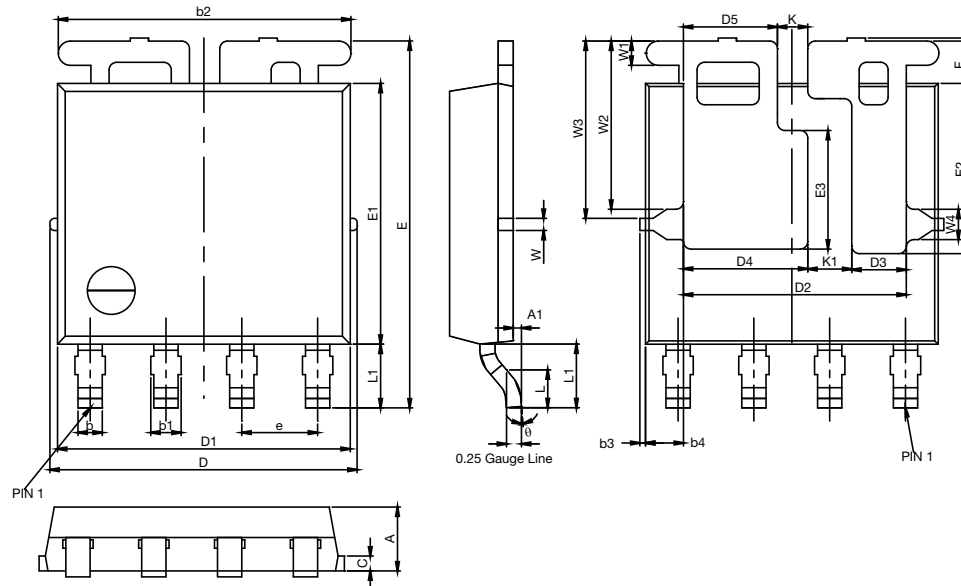
Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Case ($25\text{ }^{\circ}\text{C}$)
 are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62767.

PowerPAK® SO-8L Asymmetric Case Outline



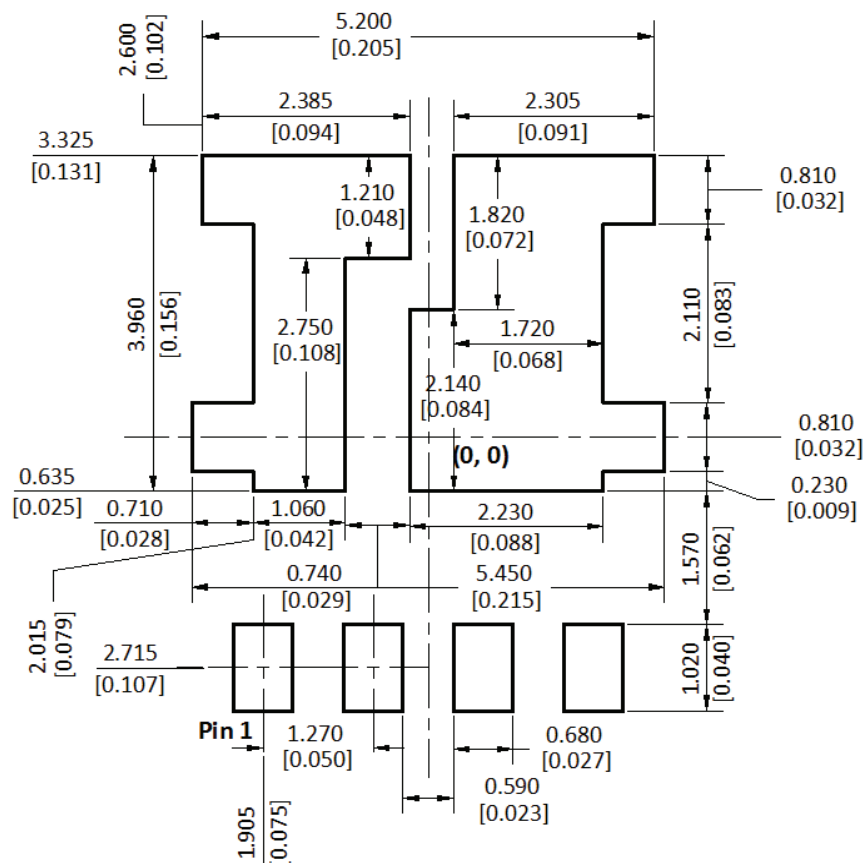
DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.00	1.07	1.14	0.039	0.042	0.045
A1	0.00	-	0.127	0.00	-	0.005
b	0.33	0.41	0.48	0.013	0.016	0.019
b1	0.44	0.51	0.58	0.017	0.020	0.023
b2	4.80	4.90	5.00	0.189	0.193	0.197
b3	0.094 typ.			0.004 typ.		
b4	0.64 typ.			0.025 typ.		
c	0.20	0.25	0.30	0.008	0.010	0.012
D	5.00	5.13	5.25	0.197	0.202	0.207
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.63	3.73	3.83	0.142	0.146	0.150
D3	0.81	0.91	1.01	0.032	0.036	0.040
D4	1.98	2.08	2.18	0.078	0.082	0.086
D5	1.47	1.57	1.67	0.058	0.062	0.066
e	1.27 BSC			0.050 BSC		
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	4.27	4.37	4.47	0.168	0.172	0.176
E2	2.75	2.85	2.95	0.108	0.112	0.116
E3	1.89	1.99	2.09	0.074	0.078	0.082
F	-	-	0.15	-	-	0.006
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
K	0.51 typ.			0.020 typ.		
K1	0.74 typ.			0.029 typ.		
W	0.23 typ.			0.009 typ.		
W1	0.41 typ.			0.016 typ.		
W2	2.82 typ.			0.111 typ.		
W3	2.96 typ.			0.117 typ.		
W4	0.51 typ.			0.020 typ.		
θ	0°	-	10°	0°	-	10°

ECN: C12-1157-Rev. B, 12-Nov-12
DWG: 6009

Note

- Millimeters will govern

RECOMMENDED MINIMUM PADS FOR PowerPAK® SO-8L DUAL ASYMMETRIC



Recommended Minimum Pads
Dimensions in mm [inches]



Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9